

Fine Pitch RF Calibration and Sensitivity to Variation for Pyramid Probe



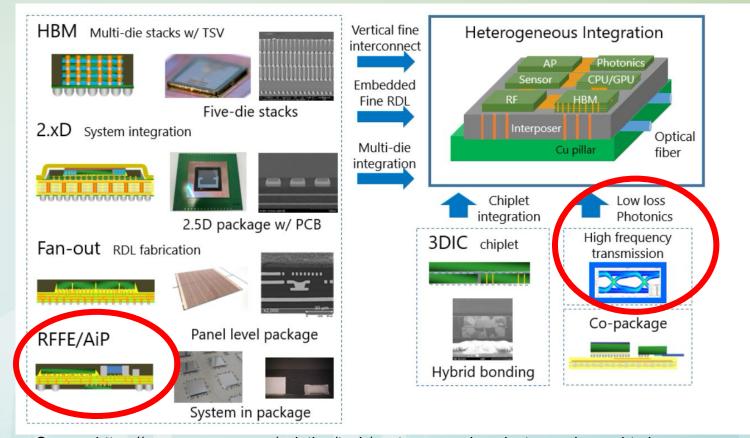
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Agenda

- Market Driver: Multi-Chip Modules (MCM)
- DOE study design
- Measurements of Calibration Standards
- Analysis and conclusions on sensitivity to process in fabrication and testing
- Final recommendations

Heterogenous Integration: Device Pitch

- Heterogenous integration of different chips into MCMs is requiring 'more finely pitched and threedimensionally integrated' modules with a larger variation of different functions combined
- The finer pitch affects all pieces in the stack-up, including the RF and High Speed Digital chips:
 - RFFE
 - AiP
 - TIAs and Laser Drivers



Source: https://www.resonac.com/solution/tech/next-gen-semiconductor-packages.html

More (Not Less) Wafer Test

'The move to multi-die packaging is driving chipmakers to develop more cost-effective ways to ensure only known-good die are integrated into packages, because the price of failure is significantly higher than with a single die.'

-Need For KGD Drives Singulated Die Screening, MARCH 31ST, 2025 - BY: <u>ANNE MEIXNER</u>, <u>SEMICONDUCTOR</u> ENGINEERING

 Therefore, excellent signal integrity probe cards, with stable calibration with low variation over time and from test cell to test cell, is needed to keep it cost effective RF Wafer Test: Pyramid Probe and ISS

- The Pyramid Probe provides excellent signal integrity for RF wafer test up to 81 GHz
 - Return loss better than 10 dB
- For the best measurements, the custom Impedance Standard Substrates (ISS) are used to do RF calibration to the tip
 - Match device layout to minimize variation



Questions about RF Calibration with Narrow Pitch?

- Some questions that people have asked about moving to narrower pitches and how it affects RF calibration include:
 - How does RF calibration vary from substrate to substrate due to process variation?
 - How does probe-to-pad alignment affect RF measurements at narrow pitch?
 - How does the pad gap affect RF measurements, where a small gap will make routing easier but will increase coupling to ground?

ISS Load DOE Variations

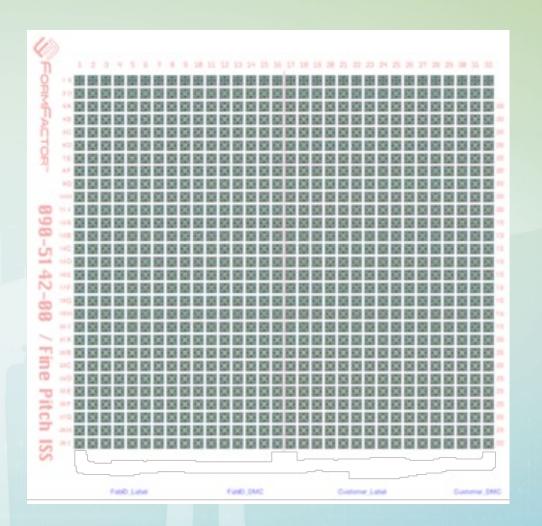
Variable	Target	Variations	
Metal Pad (Au1)	60 um	+/- 2 um	
Resistor width (Res)	40 um	+/- 1.5 um	
Pad-Ground Gap	20 um	+/- 5 um	
Probe-to-Pad Alignment*	0 um	5 um, or 10 um in X and/or Y from pad center	

^{*}This was controlled not in the design, but programmed offset with the prober

Res Skew Au1 Skew

Narrow Pitch Test: ISS Design

- To evaluate RF calibration variation, an ISS with smaller pads and loads to support narrower pitches was designed and manufactured
 - 100 um -> 80 um in GSG line
- ISS includes:
 - Loads in row 3-29
 - The rows tested all combinations of the design parameters
 - Each ISS has 864 loads
 - Loads are 50 +/- 0.5 Ohm
 - Yield of the loads was > 99%
 - Shorts in row 1 and opens in row 2 for SOL
 1-port calibration to the tip



ISS Variation Test Setup

- Pyramid Probe Card
 - RFC Pyramid Probe with 1 mm connectors on the PCB

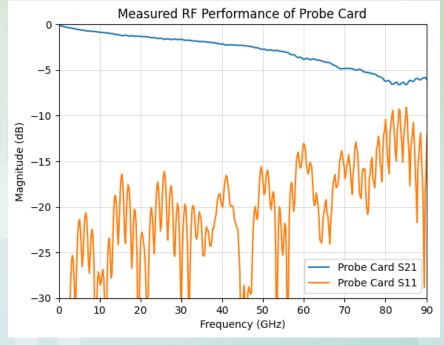


Experimental Pyramid Probe in Test Environment

- Test System:
 - Keysight PNA-X with mmW test setup up to 110 GHz
 - FormFactor 12000 station
- RF Measurements were calibration to the tip
 - Calibration standards were:
 - The load at row 3, column 1
 - The short and open in column 1



12000 Station with PNA-X mmW Test Set



Measured S-parameter Performance of the RFC Probe
Card

RF Analysis Methods

- The performance of the ISS was evaluated using two methods
 - Calculated average load inductance over frequency

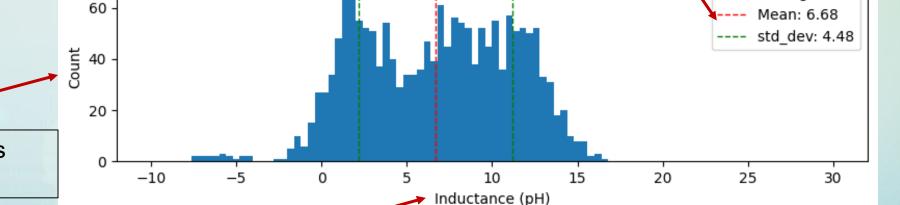
$$L_{ave} = \frac{1}{n} \sum_{i=0}^{n} \frac{Z_{im}}{2\pi f}$$

- Inductance was picked to evaluate variation because inductance directly relates to how the load is operating at RF frequencies
- Evaluated the S-parameters, comparing the mean and standard deviation of the S-parameters over the measurements

Inductance Histograms: Quick Summary

 Once the Inductance was calculated, we then plotted the histogram of the extracted inductance

Added in lines for mean and 1 standard deviation to plot, with value in legend



Histogram for SB119629.1 Substrate

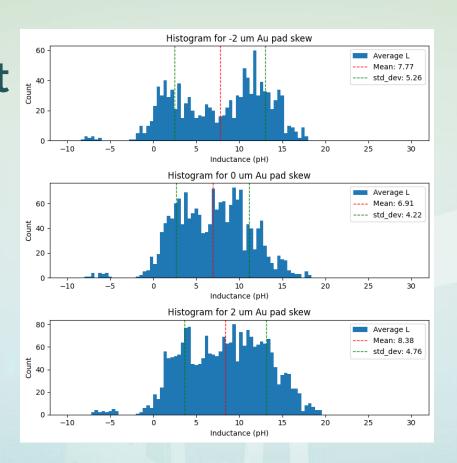
Y-axis is number (count) of loads with a given inductance

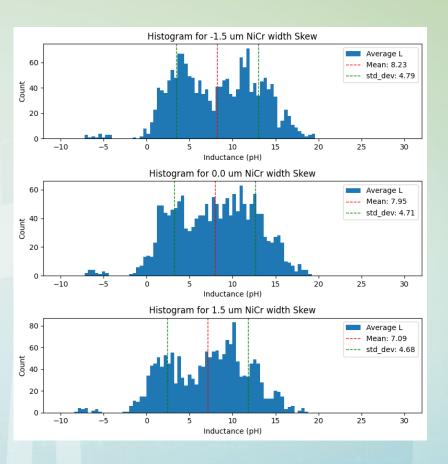
X-axis is calculated Inductance (pH)

Average L

Variation of Load: Res and Au Skew

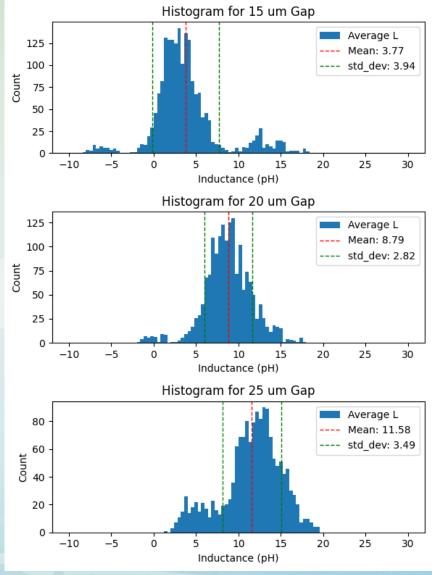
 The variation when looked at vs Au1 and Res, there was not a strong effect with the calculated inductance





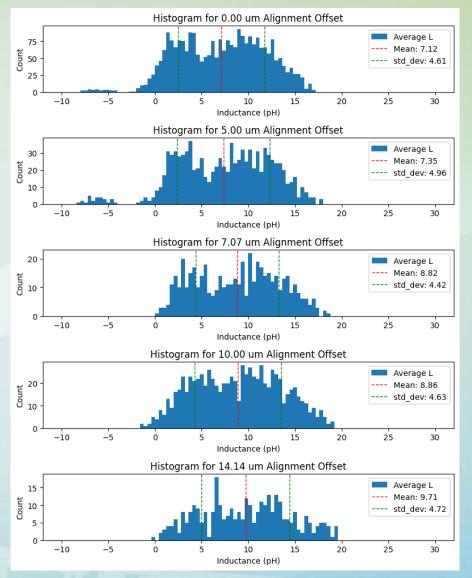
Variation of Load Inductance due to Gap

- There is a strong effect due to the gap
 - As the gap is increased from the nominal, the extracted load inductance increases
 - Or if the gap is decreased from the nominal, inductance is reduced
 - This was expected due to the amount of change: 15, 20, and 25 um gap



Variation of Load: Probe Contact Offset

- The variation in the extracted load inductance based on probe to pad alignment was not large
 - There is a small amount of increase in inductance as the offset distance was increased



Pearson's Correlation

- Looking at the extracted inductance and correlating with the various DOE factors, the gap has the largest effect
 - The probe to pad alignment (offset) has a small effect

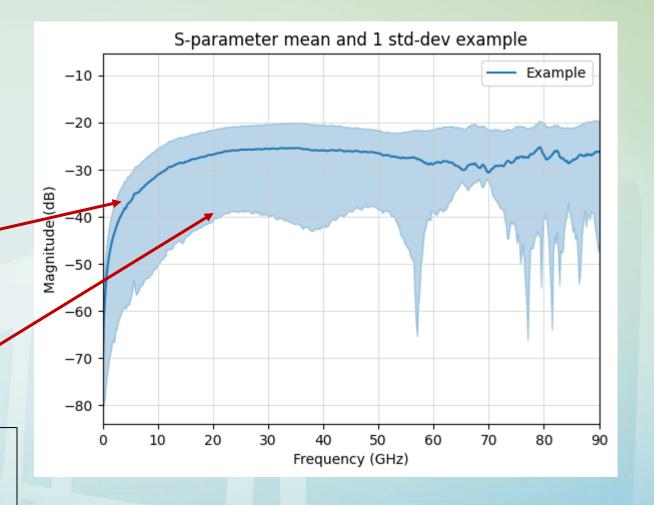
		Average L	Gap	Total offset	NiCr Skew	Au1 skew
	Average L	1.000000				
	Gap	0.675762	1.000000			
T	otal offset	0.171474	-0.000197	1.000000		
1	NiCr Skew	-0.097591	-0.000712	-0.001189	1.000000	
1	Au1 skew	0.073046	0.026617	0.000387	0.001005	1.000000

How to read the S-parameter Variation Plots

 This S-parameter uncertainty plot allows one to see the variation across frequency for a large set of data for the load measurements

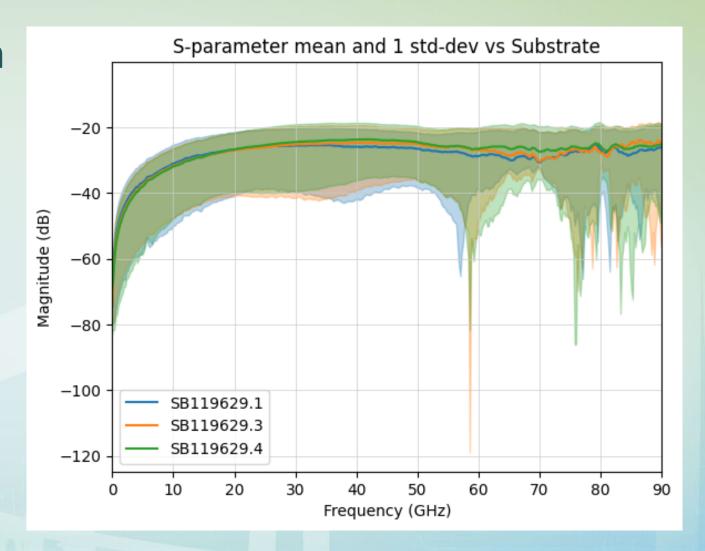
Dark line is the mean

Light shading shows 1 standard deviation of variation in the data



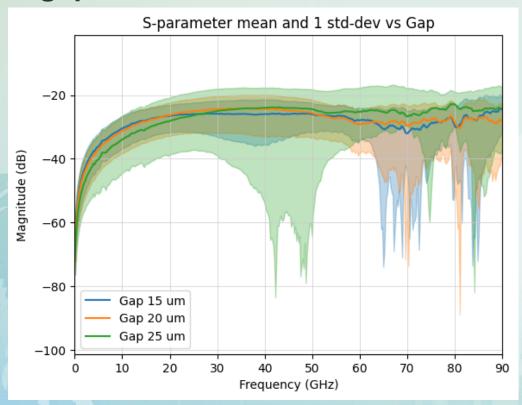
S-parameter Variation

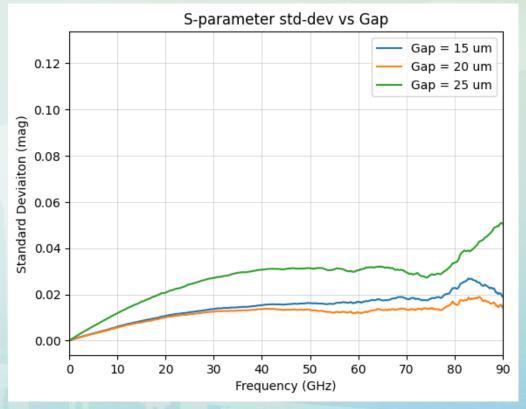
- The S-parameter variation plots show now real different vs:
 - Au1 pad skew
 - Res skew
 - Probe-to-Pad Alignment
 - Substrate



S-parameter Variation: Pad-to-Gnd Gap Effect

- The gap had the largest effect on the extracted inductance, and also had the largest effect in S-parameters
 - The standard deviation from 25 um gap was much larger than 20 and 15 um gaps





Conclusion

- Process variation in the Custom ISS will not have a large effect on the final S-parameters and extracted inductance of test structures
- The largest variation was due to the pad-to-gnd gap in both
 S-parameters and inductance calculation
 - A gap of 25 um increased variation in the S-parameter measurements when compared to 20 and 15 um
 - Recommendation is to only allow for 20 and 15 um gaps due to the increased variation in measurements with 25 um

Questions

